

MICRO

ELECTRONICS

NPN
SILICON
TRANSISTOR

TO-92F



DESCRIPTION

BSS38 is PNP silicon planar transistor designed for high voltage video amplifiers in television receivers.

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	100V
Collector-Base Voltage	V _{CBO}	120V
Emitter-Base Voltage	V _{EBO}	5V
Collector Current	I _C	100mA
Continuous Power Dissipation	P _d	300mW
Operating & Storage Junction Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

(T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	LV _{CEO}	100		V	I _C =1mA IB=0
Collector-Base Breakdown Voltage	BV _{CBO}	120		V	I _C =100μA IE=0
Emitter-Base Breakdown Voltage	BV _{EBO}	5		V	IE=100μA IC=0
Collector Cutoff Current	I _{CBO}		200	nA	V _{CB} =90V IE=0
Emitter Cutoff Current	I _{EBO}		100	nA	V _{EB} =4V IC=0
D.C. Current Gain	HFE	20			I _C =4mA V _{CE} =1V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.7	V	I _C =4mA IB=0.4mA
			3		I _C =50mA IB=15mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		1.2		I _C =4mA IB=0.4mA
Current Gain Bandwidth Product	f _T	60		MHz	I _C =4mA V _{CE} =10V
Output Capacitance	C _{ob}		4.5	pF	V _{CB} =10V f=1MHz



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